

Ultrafast Rectifier

MUR550PF

FEATURES

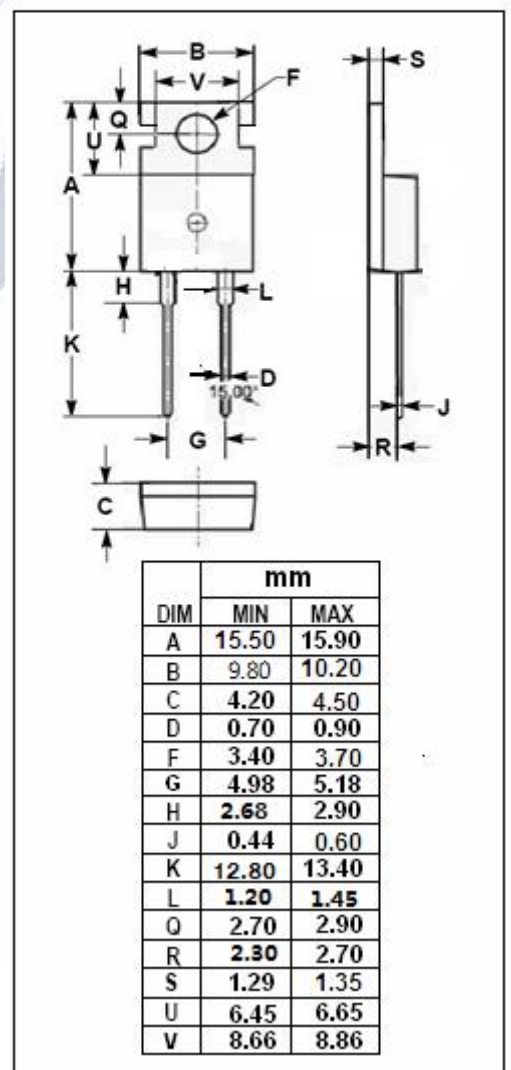
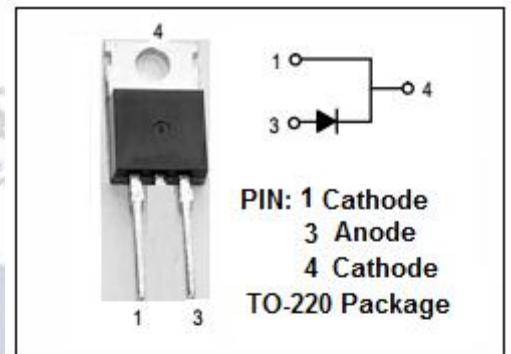
- Guarding for over voltage protection
- Dual rectifier construction, positive center tap
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching power supply
- Power switching circuits

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	520	V
$I_{F(AV)}$	Average Rectified Forward Current	5	A
I_{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	100	A
P_D	Maximum power dissipation	44.6	W
T_J	Junction Temperature	-55~175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~175	$^{\circ}\text{C}$



Fast Recovery Rectifier

MUR550PF

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-c}	Thermal Resistance, Junction to Case	2.8	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$) (Pulse Test: Pulse Width=300 μ s, Duty Cycle $\leq 2\%$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 5\text{A}; T_j = 25^{\circ}\text{C}$ $I_F = 5\text{A}; T_j = 150^{\circ}\text{C}$	1.15 0.98	V
I_R	Maximum Instantaneous Reverse Current	$V_R = V_{RWM}$ $V_R = V_{RWM}; T_j = 150^{\circ}\text{C}$	5 400	μA
t_{rr}	Maximum Reverse Recovery Time	$I_F = 1\text{A};$	95	ns